ABSTRACT

The invention relates to a method for heating a wafer (1) comprising at least one layer to be heated (2) and a sub-layer (4), under the effect of at least one light flux pulse, comprising the following steps: selecting a light flux (7), a layer to be heated (2) such that the absorption coefficient of said flux by the layer to be heated (2) is low as long as the temperature of said layer to be heated is in the low temperature range (PBT) and said absorption coefficient increases significantly when the temperature of the layer to be heated enters a high temperature range (PHT); and selecting a sub-layer (4) such that the absorption coefficient of said light flux at said selected wavelength is high in said low temperature range (PBT) and the temperature enters the high temperature range (PHT) when said sub-layer is subject to the light flux; and applying said light flux (7) to said wafer (1).

Figure 2